

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-47. (Canceled)

48. (Currently Amended) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a resinous layer formed over one of the pair of the flexible substrates;

~~a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween~~ over the resinous layer, the thin film transistor

having a ~~channel forming region~~ semiconductor film comprising silicon; and

a layer comprising resin covering the thin film transistor,

wherein the semiconductor device is flexible.

49.-51. (Canceled)

52. (Currently Amended) A semiconductor device comprising:

a pair of flexible substrates opposing to each other;

a resinous layer formed over one of the pair of the flexible substrates;

~~a thin film transistor formed between the pair of flexible substrates with a resinous layer interposed therebetween~~ over the resinous layer, the thin film transistor

having a ~~channel forming region~~ semiconductor film comprising crystalline silicon; and

a layer comprising resin covering the thin film transistor,

wherein the semiconductor device is flexible.

53.-55. (Canceled)

56. (Currently Amended) A semiconductor device comprising:
a pair of flexible substrates opposing to each other;
a resinous layer formed over one of the pair of the flexible substrates;
~~a thin film transistor formed between the pair of flexible substrates with a~~
~~resinous layer interposed therebetween~~ over the resinous layer; and
a layer comprising resin covering the thin film transistor,
wherein the thin film transistor has a ~~channel forming region~~ semiconductor film
comprising a crystalline silicon, and
wherein the crystalline silicon is formed by a laser irradiation,
wherein the semiconductor device is flexible.

57.-60. (Canceled)

61. (Currently Amended) A semiconductor device according to ~~any one of claims~~
~~47-50~~ claim 48, wherein the silicon is amorphous silicon.

62. (Currently Amended) A semiconductor device according to ~~any one of~~
~~claims 47-50~~ claim 48, wherein the silicon is microcrystalline silicon.

63. (Currently Amended) A semiconductor device according to ~~any one of~~
~~claims 39-42 and 55-58~~ claim 56, wherein the laser comprises irradiation is conducted
by using at least one selected from the group consisting of KrF excimer laser and XeCl
laser.

64-65. (Canceled)

66. (Currently Amended) A semiconductor device according to any one of claims ~~32, 34, 36, 38, 40, 42, 48, 50, 52, 54, 56 and 58~~ 48, 52 and 56, wherein the flexible substrate comprises a plastic substrate.

67. (Currently Amended) A semiconductor device according to any one of claims ~~32, 34, 36, 38, 40, 42, 48, 50, 52, 54, 56 and 58~~ 48, 52 and 56, wherein the flexible substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

68. (Currently Amended) A semiconductor device according to any one of claims ~~31-42 and 47-58~~ 48, 52 and 56, wherein the resinous layer comprises an acrylic resin.

69. (Currently Amended) A semiconductor device according to any one of claims ~~31-42 and 47-58~~ 48, 52 and 56, wherein the resinous layer comprises at least one selected from the group consisting of methyl esters of acrylic acid, ethyl esters of acrylic acid, butyl esters of acrylic acid, and 2-ethylhexyl esters of acrylic acid.

70. (Currently Amended) A semiconductor device according to any one of claims ~~31-42 and 47-58~~ 48, 52 and 56, wherein the thin film transistor comprises an inverted-staggered thin-film transistor.

71. (Currently Amended) A semiconductor device according to any one of claims ~~31-42 and 47-58~~ 48, 52 and 56, wherein the thin film transistor comprises a coplanar thin-film transistor.

72.-84. (Canceled)